			1.004	2002/04/04 40 45
-	21	(semiconductor near laser) and (active near (layer or region	USPAT;	2003/04/04 10:46
		or medium or film)) and (protection near (film or layer or	US-PGPUB;	
		region or medium)) and ridge and (refractive near (index or	EPO; JPO;	
		indice)) and (open\$5) and (shap\$4)	DERWENT;	
			IBM_TDB	
-	3	("5029175" "5474954" "5805627").PN.	USPAT	2003/04/04 10:40
-	23	(semiconductor near laser) and (active near (layer or region	USPAT;	2003/04/04 10:49
		or medium or film)) and (protection near (film or layer or	US-PGPUB;	
		region or medium)) and ridge and (refractive near (index or	EPO; JPO;	
		indice)) and (open\$5) and (shap\$4) and width	DERWENT;	
			IBM_TDB	
-	57	(semiconductor near laser) and substrate and (active near	USPAT;	2003/04/04 11:06
		(layer or region or film or medium)) and (protection near	US-PGPUB;	
		(layer or region or film or medium)) and (ridge or stripe)	EPO; JPO;	
		and (refractive near (index or indice)) and width	DERWENT;	
		,,,	IBM_TDB	
_	18	(semiconductor near laser) and substrate and (active near	USPAT;	2003/04/04 12:09
		(layer or region or film or medium)) and (protection near	US-PGPUB;	, ,
		(layer or region or film or medium)) and ((ridge or stripe)	EPO; JPO;	
		WITH (refractive near (index or indice))) and width	DERWENT;	
		(and the man of managery) and managery	IBM_TDB	
_	14	(semiconductor near laser) and substrate and (protection	USPAT;	2003/04/04 12:40
		near (layer or region or film or medium)) and ((ridge or	US-PGPUB;	
		stripe) WITH (refractive near (index or indice)) WITH	EPO; JPO;	
		(active near (layer or region or film or medium))) and width	DERWENT;	
		(delive field (dayor of region of film of filediantiff) and the	IBM_TDB	
_	405	(semiconductor near laser) and (active near (layer or region	USPAT;	2003/11/13 09:31
	.05	or medium or film)) and ((protect\$4 or dielectric) near	US-PGPUB;	
		(film or layer or region or medium)) and ridge and	EPO; JPO;	
		(refractive near (index or indice))	DERWENT;	
		(refractive fiear (findex of findice))	IBM_TDB	
l <u>.</u>	61	(semiconductor near laser) and (active near (layer or region	USPAT;	2003/11/13 10:34
		or medium or film)) and (protection near2 (film or layer or	US-PGPUB;	
		region or medium)) and ridge and (refractive near (index or	EPO; JPO;	
		indice))	DERWENT;	
		muice))	IBM_TDB	
	5	(semiconductor near laser) and (active near (layer or region	USPAT;	2003/11/14 06:09
-)	or medium or film)) and (protection near2 dielectric near2	US-PGPUB;	2003/11/17 00:03
			EPO; JPO;	
		(film or layer or region or medium)) and ridge and	DERWENT;	
		(refractive near (index or indice))		
			IBM_TDB	

or medium or film)) and (protection near (film or layer or region or medium)) and ridge and (refractive near (index or indice))	SPAT; S-PGPUB; O; JPO;	2003/11/13 09:51
region or medium)) and ridge and (refractive near (index or indice)) DE IB		
indice)) DE	∩ ≀D∩ · ା	
IB		
	RWENT;	
	M_TDB	
		2002/05/20 13:54
	-PGPUB;	
	O; JPO;	
	RWENT;	
	M_TDB	
		2002/05/20 10:37
	-PGPUB;	
or region or medium)) SAME (SUBSTRATE)) and ridge and EP	O; JPO;	
(refractive near (index or indice))	RWENT;	
	M_TDB	
		2002/05/20 15:02
or medium or film)) AND (protection near (film or layer or US	-PGPUB;	
region or medium)) SAME (SUBSTRATE)) and ridge and EP	O; JPO;	
(refractive near (index or indice))	RWENT;	
	M_TDB	
- 17 ((semiconductor near laser) and ((active near (layer or US	PAT;	2002/05/20 14:24
region or medium or film)) AND (protection near (film or US	-PGPUB;	
	O; JPO;	
	RWENT;	
	M_TDB	
		2002/05/20 14:24
	-PGPUB;	
	O; JPO;	
	RWENT;	
	M_TDB	
- 12 (semiconductor near laser) and ((active near (layer or region US	PAT;	2002/05/20 16:36
or medium or film)) AND (protection near (film or layer or US	-PGPUB;	
region or medium)) SAME (SUBSTRATE)) and (width same EP	O; JPO;	
ridge) and (refractive near (index or indice))	RWENT;	
IB	M_TDB	
- 11 ((semiconductor near laser) and ((active near (layer or US	PAT;	2002/05/21 08:26
region or medium or film)) AND (protection near (film or US	-PGPUB;	
layer or region or medium)) SAME (SUBSTRATE)) and (O; JPO;	
width same ridge) and (refractive near (index or indice))) DE	RWENT;	
	M_TDB	
		2002/05/21 10:56
	-PGPUB;	
	O; JPO;	
	RWENT;	
	M_TDB	
	, ,	2002/05/21 10:59
	-PGPUB;	
	O; JPO;	
ridge and (refractive near (index or indice)) AND substrate DE	RWENT;	
	M_TDB	
- 0 (semiconductor near laser) and (active near (layer or region US	PAT; 2	2002/05/22 13:14
	-PGPUB;	
	O; JPO;	
	RWENT;	
	M_TDB	
		2002/05/22 13:18
	-PGPUB;	
	O; JPO;	
substrate) and ridge and (refractive near (index or indice)) DE	RWENT;	
	M_TDB	

			1	
-	131	(semiconductor near laser) and (active near (layer or region	USPAT;	2002/05/22 13:21
		or medium or film)) and (((dielectric or insulat\$5 or	US-PGPUB;	
		protect\$5) near (film or layer or region or medium)) same	EPO; JPO;	
		substrate same ridge) and (refractive near (index or indice))	DERWENT;	
		and width	IBM_TDB	
-	29	(semiconductor near laser) and (active near (layer or region	USPAT;	2002/05/22 14:31
		or medium or film)) and (((dielectric or insulat\$5 or	US-PGPUB;	
		protect\$5) near (film or layer or region or medium)) same	EPO; JPO;	
		substrate same ridge same (refractive near (index or	DERWENT;	
		indice))) and width	IBM_TDB	
-	23	((semiconductor near laser) and (active near (layer or region	USPAT;	2002/05/22 14:31
		or medium or film)) and (((dielectric or insulat\$5 or	US-PGPUB;	, ,
		protect\$5) near (film or layer or region or medium)) same	EPO; JPO;	
		substrate same ridge same (refractive near (index or	DERWENT;	
		indice))) and width) and 372/\$	IBM_TDB	
_	6	((semiconductor near laser) and (active near (layer or region	USPAT;	2002/05/22 14:32
		or medium or film)) and (((dielectric or insulat\$5 or	US-PGPUB;	2002/05/22 11:52
		protect\$5) near (film or layer or region or medium)) same	EPO; JPO;	
		, , , , , , , , , , , , , , , , , , , ,	DERWENT;	
		substrate same ridge same (refractive near (index or indice))) and width) and 257/\$	IBM_TDB	
	13		USPAT;	2002/05/22 14:36
1-	12	(semiconductor near device) and (active near (layer or	US-PGPUB;	2002/03/22 14:30
		region or medium or film)) and (((dielectric or insulat\$5 or		
	La propriedo de la constanta d	protect\$5) near (film or layer or region or medium)) same	EPO; JPO;	
,		substrate same ridge same (refractive near (index or	DERWENT;	
	20	indice))) and width	IBM_TDB	2002/05/22 14.41
-	30	(semiconductor near (device or laser)) and (active near	USPAT;	2002/05/22 14:41
		(layer or region or medium or film)) and (((dielectric or	US-PGPUB;	
		insulat\$5 or protect\$5) near (film or layer or region or	EPO; JPO;	
		medium)) same substrate same ridge same (refractive near	DERWENT;	
	_	(index or indice))) and width	IBM_TDB	
-	344	(semiconductor with optical) and substrate and (active near	USPAT;	2002/05/31 10:54
		(layer or film or region or medium)) and ((protect\$5 or	US-PGPUB;	
ļ		insulat\$5) near (film or layer or region or medium)) and	EPO; JPO;	
		ridge and refractive	DERWENT;	
			IBM_TDB	
-	114	(semiconductor with optical) and substrate and (active near	USPAT;	2002/05/31 13:23
		(layer or film or region or medium)) and ((protect\$5 or	US-PGPUB;	
		insulat\$5) near (film or layer or region or medium)) and	EPO; JPO;	
		(ridge or groove) and refractive and (stripe near shaped)	DERWENT;	
			IBM_TDB	
-	0	((semiconductor with optical) and substrate and (active near	USPAT;	2002/05/31 13:33
		(layer or film or region or medium)) and ((protect\$5 or	US-PGPUB;	
		insulat\$5) near (film or layer or region or medium)) and	EPO; JPO;	
		(ridge or groove) and refractive and (stripe near shaped))	DERWENT;	
		and (open\$5 near center) and (open\$5 near rear)	IBM_TDB	
-	108	((semiconductor with optical) and substrate and (active near	USPAT;	2002/05/31 13:38
		(layer or film or region or medium)) and ((protect\$5 or	US-PGPUB,	
		insulat\$5) near (film or layer or region or medium)) and	EPO; JPO;	
		(ridge or groove) and refractive and (stripe near shaped))	DERWENT;	
		and width	IBM_TDB	
_	90	(((semiconductor with optical) and substrate and (active	USPAT;	2002/05/31 13:38
		near (layer or film or region or medium)) and ((protect\$5 or	US-PGPUB;	
		insulat\$5) near (film or layer or region or medium)) and	EPO; JPO;	
		(ridge or groove) and refractive and (stripe near shaped))	DERWENT;	
		and width) and 372/\$	IBM_TDB	
_	27	(semiconductor near laser) and (active near (layer or region	USPAT;	2002/06/18 11:28
		or medium or film)) and (protection near (film or layer or	US-PGPUB;	
		region or medium)) and ridge and (refractive near (index or	EPO; JPO;	
		indice)) and (open\$5)	DERWENT;	
		ilidice), alid (opeligs)	IBM_TDB	
	1		םעו _ויוטג	L